International **ICR** Rectifier

HEXFRED[™]

Features

- Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- · Specified at Operating Conditions

Benefits

- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- · Reduced Snubbing
- · Reduced Parts Count

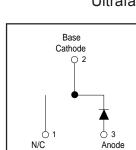
Description

International Rectifier's HFA08TB120S is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 volts and 8 amps continuous current, the HFA08TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA08TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

Absolute Maximum Ratings

	Parameter	Max.	Units
V _R	Cathode-to-Anode Voltage	1200	V
I _F @ T _C = 100°C	Continuous Forward Current	8.0	
I _{FSM}	Single Pulse Forward Current	130	A
I _{FRM}	Maximum Repetitive Forward Current	32	1
P _D @ T _C = 25°C	Maximum Power Dissipation	73.5	w
P _D @ T _C = 100°C	Maximum Power Dissipation	29	7 **
TJ	Operating Junction and	55 to 1450	°C
T _{STG}	Storage Temperature Range	-55 to +150	

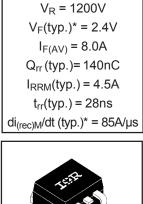
* 125°C



HFA08TB120S

Bulletin PD-20603 rev. B 11/03

Ultrafast, Soft Recovery Diode





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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions
V _{BR}	Cathode Anode Breakdown Voltage	1200			V	I _R = 100μA
	Max Forward Voltage		2.6	3.3		I _F = 8.0A
V _{FM}			3.4	4.3	V	I _F = 16A
			2.4	3.1		I _F = 8.0A, T _J = 125°C
I _{RM}	Max Reverse Leakage Current		0.31	10	μA	V _R = V _R Rated
			135	1000		T_J = 125°C, V_R = 0.8 x V_R Rated
CT	Junction Capacitance		11	20	pF	V _R = 200V
L _S	Series Inductance		8.0	.0	nH	Measured lead to lead 5mm from
						package body

Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions		
t _{rr}	Reverse Recovery Time		28			I_F = 1.0A, di _f /dt = 200A/µs, V _R = 30V		
t _{rr1}	See Fig. 5		63	95	ns	T _J = 25°C		
t _{rr2}			106	160		T _J = 125°C	I _F = 8.0A	
I _{RRM1}	Peak Recovery Current		4.5	8.0	A	T _J = 25°C		
I _{RRM2}	See Fig. 6		6.2	11		T _J = 125°C	V _R = 200V	
Q _{rr1}	Reverse Recovery Charge		140	380	nC	T _J = 25°C		
Q _{rr2}	See Fig. 7		335	880		T _J = 125°C	diғ/dt = 200A/µs	
di _{(rec)M} /dt1	Peak Rate of Fall of Recovery Current		133		A/µs	T _J = 25°C		
di _{(rec)M} /dt2	During t _b See Fig. 8		85		-π/μ5	T _J = 125°C		

Thermal - Mechanical Characteristics

	Parameter	Min.	Тур.	Max.	Units
T _{lead} 1	Lead Temperature			300	°C
R _{thJC}	Thermal Resistance, Junction to Case			1.7	κ/w
R _{thJA} ②	Thermal Resistance, Junction to Ambient			40	
Wt	Weight		2.0		g
			0.07		(oz)

① 0.063 in. from Case (1.6mm) for 10 sec

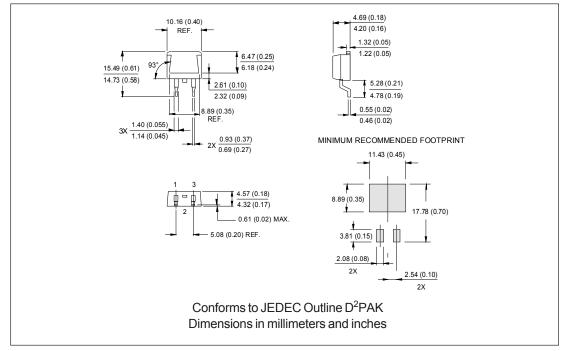
② Typical Socket Mount

International

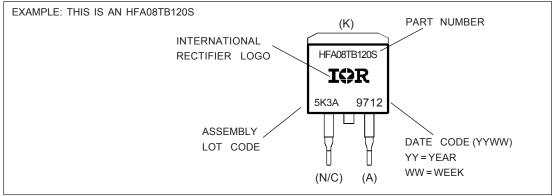
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Outline Table



Part Marking Information

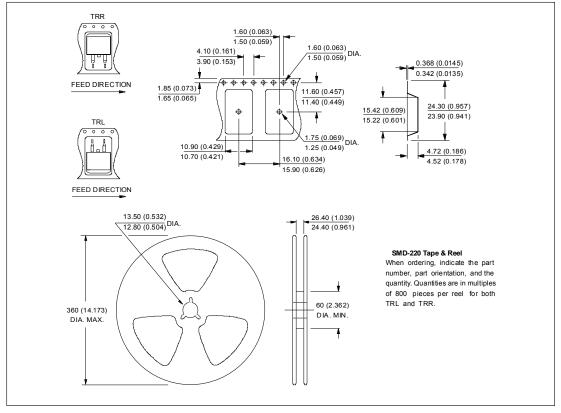


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International

Tape & Reel Information



Data and specifications subject to change without notice. This product has been designed and qualified for Industrial Level. Qualification Standards can be found on IR's Web site.

International

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